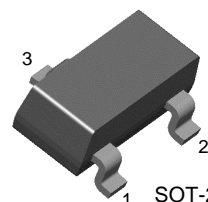


## FJV4107R

FJV4107R

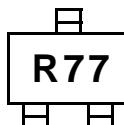
### Switching Application (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor ( $R_1=22K\Omega$ ,  $R_2=47K\Omega$ )
- Complement to FJV3107R

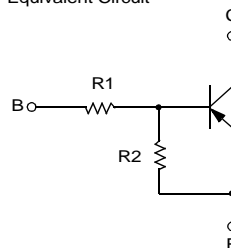


SOT-23  
1. Base 2. Emitter 3. Collector

Marking



Equivalent Circuit



### PNP Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-10	V
$I_C$	Collector Current	-100	mA
$P_C$	Collector Power Dissipation	200	mW
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

#### Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}$ , $I_E = 0$	-50			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -100\mu\text{A}$ , $I_B = 0$	-50			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -40\text{V}$ , $I_E = 0$			-0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = -5\text{V}$ , $I_C = -5\text{mA}$	68			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{mA}$ , $I_B = -0.5\text{mA}$			-0.3	V
$C_{ob}$	Output Capacitance	$V_{CB} = -10\text{V}$ , $I_E = 0$ $f = 1\text{MHz}$		5.5		pF
$f_T$	Current Gain-Bandwidth Product	$V_{CE} = -10\text{V}$ , $I_C = -5\text{mA}$		200		MHz
$V_{I(off)}$	Input Off Voltage	$V_{CE} = -5\text{V}$ , $I_C = -100\mu\text{A}$	-0.4			V
$V_{I(on)}$	Input On Voltage	$V_{CE} = -0.3\text{V}$ , $I_C = -2\text{mA}$			-2.5	V
$R_1$	Input Resistor		15	22	29	$K\Omega$
$R_1/R_2$	Resistor Ratio		0.42	0.47	0.52	

## Typical Characteristics

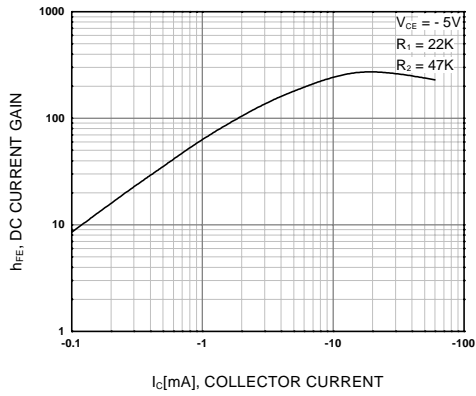


Figure 1. DC current Gain

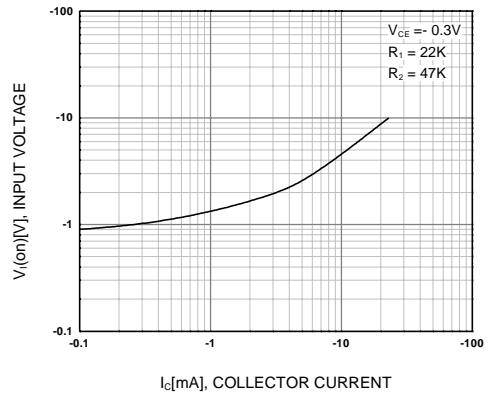


Figure 2. Input On Voltage

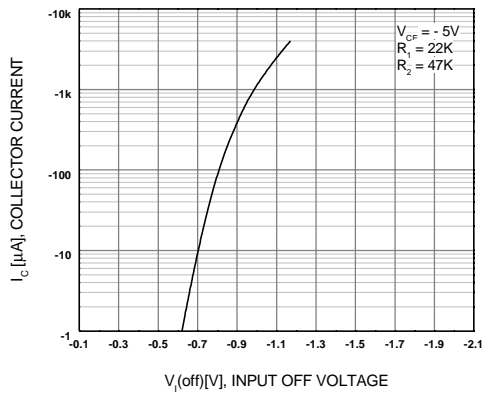


Figure 3. Input Off Voltage

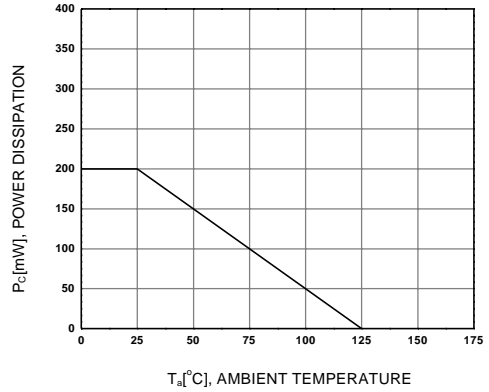
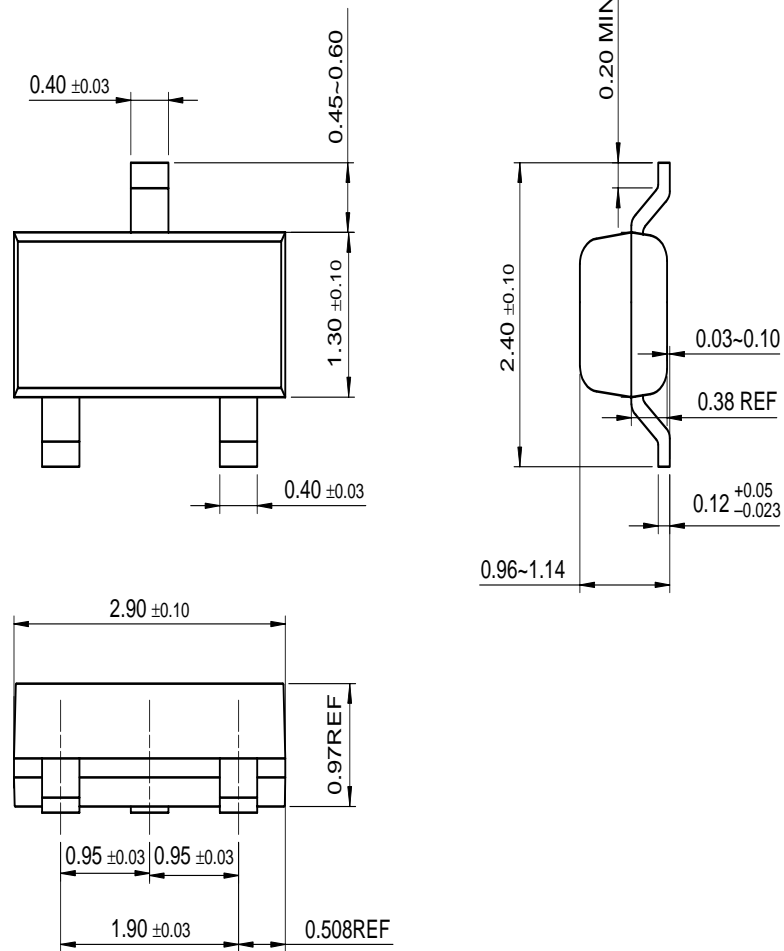


Figure 4. Power Derating

## Package Dimensions

## SOT-23



Dimensions in Millimeters

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